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ONS00470  
10/773,853Amendments to the Claims

1. (currently amended): A method for forming an isolation ~~tub~~ region comprising the steps of:  
providing a region of semiconductor material;  
forming a tub in the region of semiconductor material,  
wherein the tub includes a plurality of shapes in the region of  
semiconductor material; and  
exposing the plurality of shapes to an ambient that includes a chemical species that reacts with the plurality shapes to form the low capacitance isolation region, and wherein the plurality of shapes form part of the isolation region. ~~tub.~~
2. (currently amended): The method of claim 1 wherein the step of exposing includes thermally oxidizing the plurality of shapes to form a silicon oxide isolation region. ~~tub.~~
3. (currently amended): The method of claim 1 ~~further comprising the step of~~ wherein the step of forming the tub includes forming the tub having a boundary around the plurality of shapes, wherein the boundary includes a recessed portion.
4. (original): The method of claim 1 wherein the step of exposing includes consuming substantially all of the plurality of shapes.
5. (currently amended): The method of claim 1 further comprising the step of forming a passive device over the ~~low capacitance isolation region.~~ tub.
6. (currently amended): The method of claim 1 wherein the step of forming the ~~tub plurality of shapes~~ includes etching exposed portions of the region of semiconductor material, and wherein the plurality of shapes comprise unexposed portions of the region of semiconductor material.

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7. (original): The method of claim 6 wherein the step of etching includes etching to a depth from about 6 microns to about 10 microns.

8. (currently amended): The method of claim 1, wherein the step of forming the tub ~~plurality of shapes~~ includes forming a tub having a matrix of free standing shapes, wherein adjacent rows of shapes are offset from each other.

9. (original): The method of claim 1 wherein the step of providing the region of semiconductor material includes providing a region comprising silicon.

10. (currently amended): A process for forming an integrated circuit device including the steps of:

forming a tub region ~~a matrix of shapes~~ within a semiconductor layer, wherein tub region includes a ~~the~~ matrix of shapes comprising ~~comprises~~ offset rows; and  
forming a dielectric region within the matrix of shapes.

11. (currently amended): The process of claim 10 wherein the step of forming the tub region includes forming a tub region with a matrix of ~~shapes includes forming a matrix of~~ squares.

12. (original): The process of claim 10 wherein the step of forming the dielectric region includes oxidizing the matrix of shapes.

13. (original): The process of claim 12 wherein the step of oxidizing forms a nearly continuous silicon oxide tub.

14. (original): The process of claim 10 further comprising the step of forming a passive component over the dielectric region.

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15. (original): The process of claim 10 further comprising the step of forming an isolation trench in the region of semiconductor material.

16. (original): The process of claim 10 further comprising the steps of:

forming a dielectric layer on sidewalls of the matrix of shapes; and

forming a polycrystalline semiconductor layer over the dielectric layer.

17. (currently amended): The process of claim 10 wherein the step of forming tub region ~~the matrix of shapes~~ includes forming tub region having a matrix of shapes wherein shapes in a first row have a first spacing, and wherein the shapes in the first row have a second spacing from shapes in a second row, and wherein the second spacing is less than the first spacing.

18. (currently amended): A semiconductor device comprising:  
a region of semiconductor material; and  
a dielectric tub formed in the region of semiconductor material, wherein the dielectric tub includes comprising a matrix of passivated shapes, and wherein adjacent rows of passivated shapes are offset.

19. (original): The device of claim 18 wherein the dielectric tub comprises oxidized silicon shapes.

20. (original): The device of claim 18 wherein the dielectric tub includes a boundary having a recessed portion.

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